

LD63G5S-A/B/C-L

InGaAlP Laser Diode

Quantum Semiconductor International Co., Ltd.

ver.0 Nov. 2009

◆ OVERVIEW

LD63G5S-A/B/C-L is a MOCVD grown 635nm band InGaAlP laser diode with quantum well structure. It's an attractive light source, with a typical light output power of 15mW for optoelectronic devices such as Optical Leveler and Modules.

◆ APPLICATION

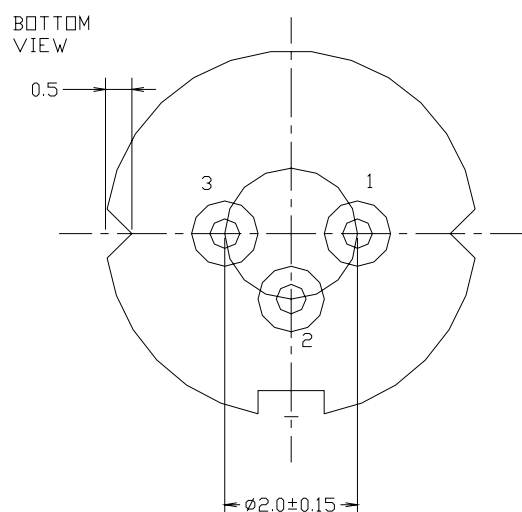
- Laser Pointer
- Optical Leveler
- Laser Module

◆ FEATURES

- Visible Light Output : $\lambda_p = 635 \text{ nm}$
- Optical Power Output : 15mW CW
- Package Type : TO-18 (5.6mm ϕ)
- Built-in Photo Diode for Monitoring Laser Diode

◆ ELECTRICAL CONNECTION

Bottom View



Pin Configuration

A	LD cathode, PD anode (Fig. 1)
B	LD , PD anode (Fig. 2)
C	LD anode, PD cathode (Fig. 3)

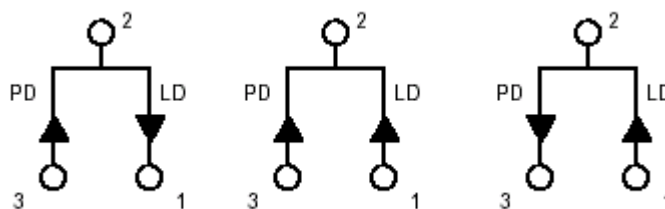


Fig. 1

LD63G5SA-L

Fig. 2

LD63G5SB-L

Fig. 3

LD63G5SC-L

◆ ABSOLUTE MAXIMUM RATING at Tc=25°C

Items	Symbols	Values	Unit
Optical Output Power	P	18	mW
Laser Diode Reverse Voltage	V	2	V
Photo Diode Reverse Voltage	V	30	V
Operating Temperature	Topr	-10 ~ +50	°C
Storage Temperature	Tstg	-40 ~ +85	°C

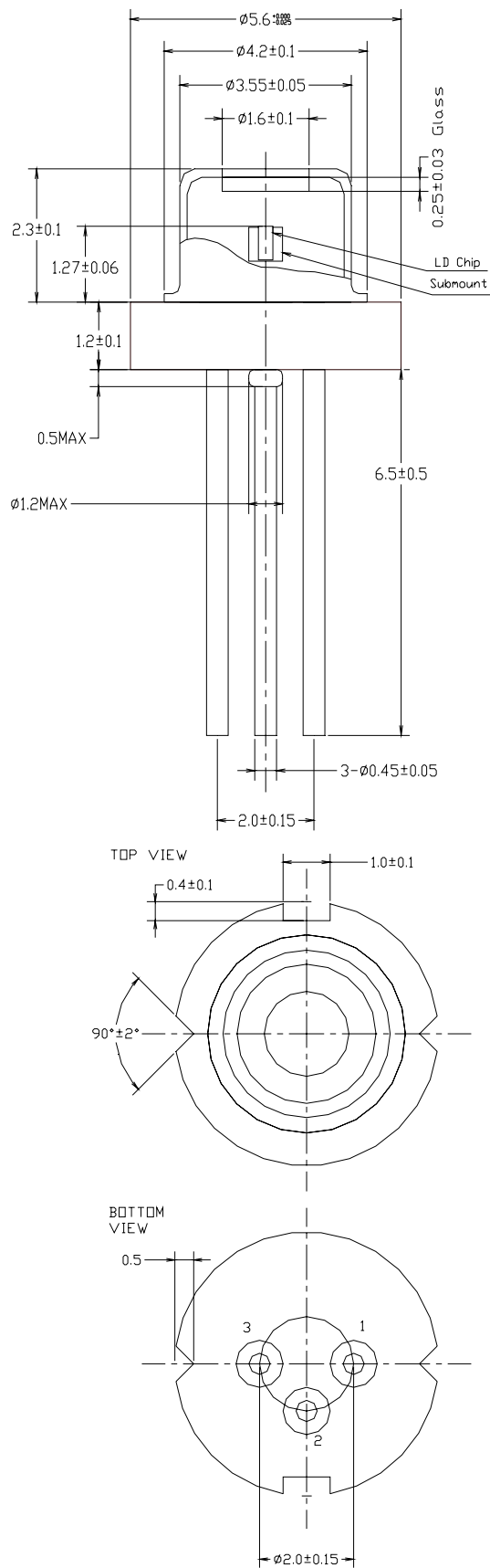
◆ ELECTRICAL and OPTICAL CHARACTERISTICS at Tc=25°C

Items	Symbols	Min.	Typ.	Max.	Unit	Condition
Optical Output Power	Po	-	15	-	mW	-
Threshold Current	Ith	-	30	40	mA	-
Operating Current	Iop	-	50	65	mA	Po=15mW
Operating Voltage	Vop	-	2.3	2.6	V	Po=15mW
Lasing Wavelength	λ_p	-	639	645	nm	Po=15mW
Beam Divergence	$\theta_{ }$	6	9	13	deg	Po=15mW
	θ_{\perp}	25	30	35	deg	Po=15mW
Beam Angle	$\Delta\theta_{ }$	-	-	±2.0	deg	Po=15mW
	$\Delta\theta_{\perp}$	-	-	±3.0	deg	Po=15mW
Monitor Current	Im	0.05	0.15	0.5	mA	Po=15mW
Optical Distance	$\Delta X, \Delta Y, \Delta Z$	-	-	±60	μm	

NOTICE : LD63G5S-A/B/C-L to be operated on APC

The above product specifications are subject to change without notice.

◆ PACKAGE DIMENSION



◆ PACKING

